Program

International Conference on Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors

(ULSIC VS TFT 8)

May 14-18, 2023

Grand Park Hotel Otaru (Sapporo), Japan

Conference Chair

Yue Kuo
Texas A&M University, USA





Engineering Conferences International
369 Lexington Avenue, 3rd Floor #389 - New York, NY 10017, USA
www.engconfintl.org - info@engconfintl.org

Grand Park Otaru

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Previous conferences in this series

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors July 29-Aug 3, 2007 Barga, Italy

Conference Chairs:

Yue Kuo, Texas A&M University, USA Michael Shur, Rensselaer Polytechnic Institute, USA Dieter Ast, Cornell University, USA

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors II July 5-10, 2009

Xi'an, China

Conference Chairs:

Yue Kuo, Texas A&M University, USA Michael Shur, Rensselaer Polytechnic Institute, USA Dieter Ast, Cornell University, USA William Milne, Cambridge University, UK Shaozhen Xiong, Nankai University, China

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors III
June 26-July 1, 2011

Hong Kong, China

Conference Chairs:

Yue Kuo, Texas A&M University, USA Gennadi Bersuker, Sematech, USA

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors IV

July 8-11, 2013

Grenoble, France

Conference Chairs:

Yue Kuo, Texas A&M University, USA Gennadi Bersuker, Sematech, USA C. Claeys, IMEC, Belgium

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors V June 14-18, 2015

Lake Tahoe, California, USA

Conference Chairs:

Yue Kuo, Texas A&M University, USA Gennadi Bersuker, Sematech, USA Olivier Bonnaud, University of Rennes, France

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors VI May 21-25, 2017

Hernstein, Austria

Conference Chairs:
Yue Kuo, Texas A&M University, USA
Olivier Bonnaud, University of Rennes, France

Semiconductor Technology for Ultra Large Scale Integrated Circuits and Thin Film Transistors VII May 19-23, 2019 Kyoto, Japan

Conference Chairs:

Yue Kuo, Texas A&M University, USA
Prof. Junichi Murota, Tohoku University, Japan
Prof. Yukiharu Uraoka, Nara Advanced Institute of Science and Technology

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Sunday, May 14, 2023

17:30 – 19:00	Conference Check-in (Foyer outside Jukai Room, 5 th Floor)
19:00 – 19:30	Welcome Reception (Foyer outside Rysei Room, 5 th Floor)
19:30 – 20:30	Dinner (Ryusei Room)
20:30 – 21:30	Free communication

Locations and Notes

- Technical Sessions will be in Jukai Room.
- Meal locations are noted in the program.
- Covid-19 precautions: Covid-19 has not gone away and we request that you be mindful of those who may be particularly vulnerable. Please bring your own test kits and masks. ECI will have a limited number of masks on hand. Masks are not required but we encourage you to use them particularly during poster sessions as there is typically a great deal of close-up discussion. If you are not feeling well, please remain in your room.
- Audiotaping, videotaping and photography of presentations are prohibited.
- Speakers Please have your presentation loaded onto the conference computer prior to the session start (preferably the day before).
- Speakers Please leave at least 3 minutes for questions
- Please do not smoke at any conference functions.
- Turn your mobile phones to vibrate or off during technical sessions.
- After the conference, ECI will send an updated participant list to all participants. Please check
 your listing now and if it needs updating, you may correct it at any time by logging into your ECI
 account.
- Emergency Contact Information: Because of privacy concerns, ECI does not collect or maintain emergency contact information for conference participants. If you would like to have this information available in case of emergency, please use the reverse side of your name badge.

Monday, May 15, 2023

06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
08:00 – 08:05	Open remark Yue Kuo, Texas A&M University
	Session: General Topics Chair: Yue Kuo, Texas A&M University
08:05 – 08:30	Invited Challenge to next-generation VLSI with VFET using oxide semiconductor and 3D structure Shunpei Yamazaki, Semiconductor Energy Laboratory Co., Ltd
08:30 – 08:55	Invited ULSI and TFT technologies joint forces to meet the future challenges of a pervasive digital society Olivier Bonnaud, University of Rennes
	Session: Semiconductor Materials Chairs: Kenji Nomura, University of California San Diego Laurie E. Calvet, LPICM, CNRS-Ecole Polytechnique Shinji Migita, AIST
08:55 – 09:20	Invited Atomic-order surface reaction of reactant gas on group IV semiconductor (100) surface Junichi Murota, Tohoku University
09:20 – 09:45	Invited Formation and luminescence studies of Ge/Si core-shell quantum dots Seiichi Miyazaki, Katsunori Makihara, Yuki Imai, Nagoya University
09:45 – 10:10	Invited Epitaxy and heterostructure of germanium tin-related group-IV alloy semiconductors for future electronic and optoelectronic applications Osamu Nakatsuka, Masashi Kurosawa, Shigehisa Shibayama, Mitsuo Sakashita, Nagoya University
10:10 – 10:40	Coffee Break
10:40 – 11:00	Crystallinity of In-Ga-Zn-oxide (IGZO) in CAAC-IGZO vertical FET Tomonori Nakayama, Yukinori Shima, Toshikazu Ono, Nao Sorida, Naoki Okuno, Hitoshi Kunitake, Shunpei Yamazaki, Semiconductor Energy Laboratory Co., Ltd.
11:00 – 11:20	Spinel, an overlooked crystalline phase of Igzo Hendrik F.W. Dekkers, Akhilesh Kumar Mandal, Evangelos Aggiannis, Adrian Vaisman, Chasin Romain Delhougne, Attilio Belmonte, Gouri Sankar Kar, Interuniversity Microelectronics Centre (imec)

Monday, May 15, 2023 (continued)

	Session: P-channel Oxide Materials for TFTs Chair: Olivier Bonnaud, University of Rennes
11:20 – 11:45	Invited Progress of p-channel oxide-TFT development and how we improve the performances Kenji Nomura, University of California San Diego
11:45 – 12:10	Invited P-channel metal oxide thin film transistors for flexible CMOS logic: Challenges and opportunities Andrew Flewitt, Kham Niang, Daisy Gomersall, Jake Meeth, Niels van Fraassen, Sanggil Han, University of Cambridge; James Parish, Andrew Johnson, University of Bath
12:10 – 14:00	Lunch (Ryusei Room)
	Session: Dielectrics Chairs: Cheol Seong Hwang, Seoul National University Junichi Murota, Tohoku University
14:00 – 14:25	Invited What can we do with ferroelectric gate? Eisuke Tokumitsu, Japan Advanced Institute of Science and Technology
14:25 – 14:50	Invited Material challenges in HfO2-based ferroelectric memory devices Min Hyuk Park, Seoul National University
14:50 – 15:15	Invited Ferroelectric phase transformation accelerated in nanolaminate HfO2-ZrO2 thin films Shinji Migita, The National Institute of Advanced Industrial Science and Technology (AIST)
15:15 – 15:45	Coffee Break
15:45 – 16:10	Invited Ternary amorphous oxide semiconductor material toward 3D-integrated ferroelectric devices Takanori Takahashi, Mutsunori Uenuma, Nara Institute of Science and Technology; Masaharu Kobayashi, University of Tokyo; Yukiharu Uraoka, Nara Institute of Science and Technology
16:10 – 16:35	Invited Microfabrication of BiTeSb thermoelectric devices for applications to IoT sensors Takahito Ono, Tohoku University
16:35 – 18:30	Free Communication
18:30 – 20:30	Dinner (Ryusei Room)
20:30 – 21:30	Panel Discussion: Challenges in TFT Materials

Tuesday, May 16, 2023

06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
	Session: Devices and Circuits I Chairs: Hitoshi Kunitake, Semiconductor Energy Laboratory Co., Ltd I-Chun Cheng, National Taiwan University Radu A. Sporea, University of Surrey
08:00 – 08:25	Invited HfZrO-based ferroelectric capacitors and FETs for ultralow-power signal processing Shinichi Takagi, Kasidit Toprasertpong, Eishin Nako, Xuan Luo, Mitsuru Takenaka, Ryosho Nakane, The University of Tokyo
08:25 – 08:50	Invited Contact effects towards mainstream thin-film transistor applications Radu A. Sporea, University of Surrey
08:50 – 09:15	Invited Latch-up issue between high-voltage circuit domain and low-voltage circuit domain in TFT LCD driver IC fabricated with BCD process Ming-Dou Ker, Zi-Hong Jiang, National Yang Ming Chiao Tung University
09:15 – 09:40	Invited Poly-oxide Tft for flexible electronics Jin Jang, Kyung Hee University
09:40 – 10:05	Invited ALD of robust amorphous oxide TFTS with turn on at the Boltzmann limit Rebecca L. Peterson, Christopher R. Allemang, Tonglin L. Newsom, Tae H. Cho, Neil P. Dasgupta, University of Michigan
10:05 – 10:30	Coffee Break
10:30 – 10:55	Invited TFT circuits for driving sensors and actuators on flat panels Florian De Roose, Nikolas Papadopoulos, Raf Appeltans, Paul Heremans, Interuniversity Microelectronics Centre (imec)
10:55 – 11:20	Invited CMOS inverters and circuits based on oxide thin-film transistors I-Chun Cheng, Shu-Ming Hsu, Yun-Shiuan Li, Wei-Chen Li, Feng-Yu Tsai, Jian-Zhang Chen, National Taiwan University
11:20 – 11:40	Device layout dependence of PBTI in back-gated IGZO TFTs Pietro Rinaudo, Adrian Chasin, Jacopo Franco, Ben Kaczer, Ingrid de Wolf, Gouri Kar, imec and Katholieke Universiteit Leuven
11:40 – 13:00	Lunch (Ryusei Room)

Tuesday, May 16, 2023 (continued)

	Session: Devices and Circuits II Chairs: Mamoru Furuta, Kochi University of Technology Po-Tsun Liu, National Yang Ming Chiao Tung University
13:00 – 13:25	Invited Vertical channel-all-around IGZO FET for low latency, high-density 2T0C 3D DRAM application Di Geng, Chuanke Chen, Xinlv Duan, Ling Li, Institute of Microelectronics of the Chinese Academy of Sciences
13:25 – 13:50	Invited Circuit architecture and pixel array driving methods for AMOLED and Mini/Micro-LED displays Chih-Lung Lin, National Cheng Kung University
13:50 – 14:15	Invited An atomistic understanding of the oxygen vacancies in Pt/TiO2/Ti resistive random access memory: Ab initio study Jung-Hae Choi, Taeyoung Jeong, Korea Institute of Science and Technology; Cheol Seong Hwang, Seoul National University
14:15 – 14:40	Invited An overview of the three-dimensionally stacked dynamic random access memory Cheol Seong Hwang, Seoul National University
14:40 – 15:10	Coffee Break
15:10 – 15:30	Tri-layer self-aligned structure indium gallium zinc oxide thin film transistor with optical synaptic plasticity <u>Tsung-Che Chiang</u> , Zhen-Hao Li, Jing-Zhong Deng, Po-Tsun Liu, National Yang Ming Chiao Tung University; Yue Kuo, Texas A&M University
15:30 – 15:55	Invited Ultrathin organic transistors toward next-generation skin electronics Sunghoon Lee, Tomoyuki Yokota, Takao Someya, The University of Tokyo
15:55 – 16:15	GAP-type low-temperature polycrystalline silicon thin film transistors for light sensing photo-transistor application Jo-Lin Chen, Tsung-Che Chiang, Zhen-Hao Li, Yu-Ting Tsai, Po-Tsun Liu, National Yang Ming Chiao Tung University; Yue Kuo, Texas A&M University
16:15 – 18:00	Free Communication
18:00 – 20:00	Dinner (Ryusei Room)
20:00 – 21:30	Poster session (Remove posters at 21:30) Chairs: Jen-Sue Chen, National Cheng Kung University

Wednesday, May 17, 2023

06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
	Session: Processes Chairs: Rebecca L. Peterson, University of Michigan Chih-Lung Lin, National Cheng Kung University
08:00 – 08:25	Invited New development on plasma-based copper etch at room temperature Yue Kuo, Texas A&M University
08:25 – 08:50	Invited Solid-phase crystallization of hydrogen-doped indium oxide for low-temperature processed TFTs Mamoru Furuta, Kochi University of Technology
08:50 – 09:10	Base pressure controlled fabrication of high-mobility In2O3 thin film transistors Yusaku Magari, Prashant Ghediya, Hui Yang, Hokkaido University; Yuqiao Zhang, Jiangsu University; Yasutaka Matsuo, Hiromichi Ohta, Hokkaido University
09:10 – 09:30	Solution processed ultrawide bandgap insulator to semiconductor conversion of amorphous gallium oxide via fermi level control Juan Paolo Bermundo, Nara Institute of Science and Technology; Diki Purnawati, Universitas Gadjah Mada; Paul Rossener Regonia, University of the Philippines Diliman; Kazushi Ikeda, Yukiharu Uraoka, Nara Institute of Science and Technology
09:30 – 09:55	Invited Developing low-temperature defect passivation technology with supercritical fluid technology Po-Hsun Chen, R.O.C. Naval Academy; Ting-Chang Chang, Pei-Yu Wu, Jian-Jie Chen, Chuan-Wei Kuo, Sheng-Yao Chou, Yu-Bo Wang, Hung-Ming Kuo, National Sun Yat-Sen University
09:55 – 10:25	Coffee Break
	Session: Novel TFT Applications Chairs: Jin Jang, Kyung Hee University
10:25 – 11:50	Panel Discussion: Challenges in TFT Applications
11:50	Pick up boxed lunches (Foyer outside of Jukai Room)
12:30 – 18:30	Optional Excursion
18:30 – 19:00	Reception (Foyer outside Rysei Room, 5 th Floor)
19:00 – 21:00	Banquet and Poster Award Announcement (Ryusei Room)
21:00 – 22:00	Free Communication

Thursday, May 18, 2023

06:30 - 08:00	Breakfast (Terrace Brasserie Restaurant)
	Session: Novel TFT Applications Chairs: Yukiharu Uraoka, NAIST Florian De Roose, imec
08:00 – 08:25	Invited Spiking neuron circuits in ULSIC vs TFT technologies Laurie E. Calvet, LPICM, CNRS-Ecole Polytechnique; Zonglong Li, Centre de Nanosciences et Nanotechnologies; Benjamin Iniguez, University Rovira i Virgili; Kruno Romanjek, CEA-LITEN
08:25 – 08:50	Invited Metal-oxide thin-film transistor: An enabling technology for smart sensor construction and 3-D monolithic integration Zhihe Xia, Yushen Hu, Tengteng Lei, Man Wong, The Hong Kong University of Science and Technology
08:50 – 09:15	Invited Temporal information processing for in-sensor computing based on amorphous IGZO phototransistor Jen-Sue Chen, Ching-Hsiang Yang, Li-Chung Shih, National Cheng Kung University
09:15 – 09:40	Invited TFT-based active sensors and sensor interfaces Kai Wang, Sun Yat-sen University
09:40 – 10:10	Coffee Break
10:10 – 10:35	Invited Organic electrochemical transistors for sensing applications Feng Yan, The Hong Kong Polytechnic University
10:35 – 11:00	Invited Droplets driving and sensing pixel circuits for thin film transistor-based digital microfluidics Dongping Wang, Chunyu Chang, Chinese Academy of Sciences; Yingbo Wei, Jun Yu, Arokia Nathan, Shandong University; Hanbin Ma, Chinese Academy of Sciences
11:00 – 11:25	Invited Mesoporous titania based synaptic device characteristics Hyun Ho Lee, Myongji University
11:25 – 11:50	Invited Characteristics of oxide TFT using atomic-layer deposited InO _x -based metal oxide channel Toshihide Nabatame, Riku Kobayashi, Kazuhito Tsukagoshi, National Institute for Materials Science
11:50 – 12:00	End of Meeting Remark
12:00	Lunch (Ryusei Room)

Poster Presentations

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Engineering Conferences International

Poster Presentations

1. Extract coefficients of thermal expansion of TaN thin film by tuning the N_2 gas flow in the PVD process

<u>Yao-Zih Lai</u>, Weileun Fang, National Tsing Hua University, Yu-Chen Hsin, Industrial Technology Research Institute

2. Highly sensitive broadband phototransistors based on gradient tin/lead mixed thin film perovskites

Hok-Leung Loi, Feng Yan, The Hong Kong Polytechnic University

3. Ultra-sensitive and portable organic electrochemical transistors for noninvasive saliva glucose monitoring

Zeyu Zhao, Feng Yan, The Hong Kong Polytechnic University

4. Flexible lon-selective biosensors for sweat analysis

Zhiyuan Tian, Feng Yan, The Hong Kong Polytechnic University

5. Vertical oxide semiconductor field-effect transistor with extremely low off-state current

<u>Takeya Hirose</u>, Tomonori Nakayama, Masataka Nakada, Manabu Sato, Tomoaki Atsumi, Masahiro Takahashi, Satoru Saito, Hitoshi Kunitake, Hideaki Shishido, Takanori Matsuzaki, Shunpei Yamazaki, Semiconductor Energy Laboratory Co., Ltd.

6. Analysis of carrier injection under high temperature AC operation in top gate IGZO TFTs

<u>Kuan-Ju Zhou</u>, Ting-Chang Chang, National Sun Yat-Sen University. Po-Hsun Chen, Military Academy. Bo-Shen Huang, National Sun Yat-Sen University. Simon M. Sze, National Yang Ming Chiao Tung University

7. Clean dry etching of Cu and Ni alloy metal thin film by reactive proton assisted etching

MunPyo Hong, Donghoon Kim, Sangheon Lee, Minyoung Kim, Sungyoun Lee, Jin Nyoung Jang, Jong Hwa Lee, Chiwoo Kim, Sang-Gab Kim, Korea University

8. Room temperature gas sensing with a hybrid poly-Si/ZnO TFT cell

<u>Horng-Chih Lin</u>, Jen-Chi Liao, Ping-Che Liu, Pei-Wen Li, National Yang Ming Chiao Tung University

9. Donor activation in boron and phosphorus implanted self-aligned bottom-gate Igzo

<u>Eli Powell</u>, Muhammad Kabir, Rahnuma Chowdhury, Karl Hirschman, Rochester Institute of Technology. Robert Manley, Bin Zhu, Corning Incorporated

10. Ambipolar oxide thin-film transistor-based artificial synapses

Chihsin Huang, Kenji Nomura, University of California San Diego

11. Hafnium oxide-based ferroelectric thin-film transistor with a-InGaZnO channel fabricated at temperatures <= 350°C

<u>Che-Chuan Lee,</u> Chun-Wei Chang, Min-Hung Lee, I-Chun Cheng, National Taiwan University

12. **P-type tin monoxide thin-film transistors on cellulose nanopaper substrates**<u>You-Hong Zhang.</u> Pu-Yuan Lin, Feng-Cheng Chang, I-Chun Cheng, National Taiwan
University

13. Electrical performance of amorphous IGZO thin-film transistor on cellulose nanopaper substrate

Zi-Fan Cao, Chih-Han Tseng, Feng-Cheng Chang, I-Chun Cheng, National Taiwan University